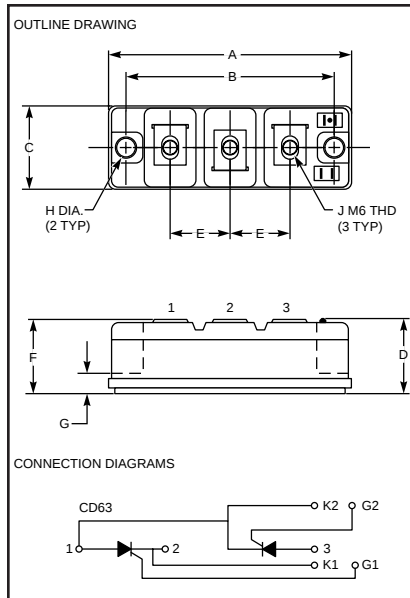


Dual SCR POW-R-BLOK™ Module 150 Amperes/1600 Volts



Outline Drawing

Dimension	Inches		Metric	
	Min.	Max.	Min.	Max.
A	3.681	3.721	93.50	94.51
B	3.145	3.155	79.88	80.14
C	1.329	1.349	33.76	34.26
D	1.181	1.240	30.00	31.50
E	0.901	0.911	22.88	23.14
F	1.161	1.201	29.49	30.51
G	0.305	0.325	7.75	8.26
HØ	0.251	0.261	6.38	6.63
J	—	—	M6 x 1.0	



CD63_ _15
Dual SCR POW-R-BLOK™ Module
150 Amperes/1600 Volts

Ordering Information:

Select the complete eight digit module part number you desire from the table below.

Example: CD631215 is a 1200 Volt, 150 Ampere Dual SCR POW-R-BLOK™ Module.

Type	Voltage Volts (x100)	Current Rating Amperes (x10)
CD63	08	15
	12	
	14	
	16	

Description:

Powerex Dual SCR Modules are designed for use in applications requiring phase control and isolated packaging. The modules are isolated for easy mounting with other components on a common heatsink. POW-R-BLOK™ has been tested and recognized by the Underwriters Laboratories (QQQX2 Power Semiconductors).

Features:

- ☐ Electrically Isolated Heatsinking
- ☐ Compression Bonded Elements
- ☐ Metal Baseplate
- ☐ Low Thermal Impedance
- ☐ Quick Connect Gate Terminal with Provision for Keyed Mating Plug
- ☐ UL Recognized 

Applications:

- ☐ Battery Supplies
- ☐ Bridge Circuits
- ☐ AC and DC Motor Control
- ☐ Tap Changers
- ☐ Lighting Control

CD63_15

Dual SCR POW-R-BLOK™ Module

150 Amperes/1600 Volts

Absolute Maximum Ratings

Characteristics	Symbol	Conditions	CD63_15	Units
Repetitive Peak Forward Blocking Voltage	V_{DRM}	—	1600	Volts
Repetitive Peak Reverse Blocking Voltage	V_{RRM}	—	1600	Volts
Non-Repetitive Peak Forward Blocking Voltage	V_{DRM}	—	$V_{DRM} + 100$	Volts
Non-Repetitive Peak Reverse Blocking Voltage	V_{RSM}	—	$V_{RRM} + 100$	Volts
RMS Forward Current	$I_{T(RMS)}$	—	250	Amperes
Average Forward Current	$I_{T(AV)}$	180° Conduction, $T_C = 89^\circ\text{C}$	150	Amperes
Peak Half-Cycle Surge (Non-Repetitive) On-State Current	I_{TSM}	$t = 8.3\text{ms}$, 100% V_{RRM} Reapplied	4500	Amperes
		$t = 10\text{ms}$, 100% V_{RRM} Reapplied	4300	Amperes
i^2t (for Fusing) for One-Cycle	i^2t	$t = 8.3\text{ms}$, 100% V_{RRM} Reapplied	84400	A^2sec
		$t = 10\text{ms}$, 100% V_{RRM} Reapplied	92500	A^2sec
Maximum Rate-of-Rise of On-State Current (Non-Repetitive)*	di/dt	$I_{TM} = \pi I_{T(AV)}$, $t_r < 0.5\mu\text{s}$, $t_p > 6\mu\text{s}$	500	Amperes/ μs
Storage Temperature	T_{STG}	—	-40 to 150	$^\circ\text{C}$
Operating Temperature	T_j	—	-40 to 125	$^\circ\text{C}$
Maximum Mounting Torque M6 Mounting Screw	—	—	4 to 6	Nm
Maximum Mounting Torque M6 Terminal Screw	—	—	4 to 6	Nm
Module Weight (Typical)	—	—	500	Grams
			17.8	oz.
V Isolation	V_{RMS}	—	3000	Volts

* $T_j = 125^\circ\text{C}$, $I_G = 500\text{mA}$, $V_D = 0.67 V_{DRM}$ (Rated)

CD63 _ _15
Dual SCR POW-R-BLOK™ Module
 150 Amperes/1600 Volts

Electrical and Thermal Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

			CD63_ _15			
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Blocking State Maximums						
Forward Off-State Current, Peak	I _{DRM}	T _j = 125°C, V _D = V _{DRM}	—	—	50	mA
Reverse Off-State Current, Peak	I _{RRM}	T _j = 125°C, V _R = V _{RRM}	—	—	50	mA
Conducting State Maximums						
Peak On-State Voltage	V _{TM}	T _j = 125°C, I _{TM} = 500A, Duty Cycle < 0.1%	—	—	1.50	Volts
Peak On-State Voltage Coefficients, Full Range	V _{TM}	T _j = 125°C, I = 15% I _{T(AV)} to I _{TSM} V _T = A + B Ln I _T + C I _T + D Sqrt I _T	A = 0.873 B = -0.0776 C = 0.000434 D = 0.0409			
Threshold Voltage, Low-Level	V _{(TO)1}	T _j = 125°C,	—	—	0.837	Volts
Slope Resistance, Low-Level	r _{T1}	I = 15% I _{T(AV)} to πI _{T(AV)}	—	—	1.34	mΩ
Threshold Voltage, High-Level	V _{(TO)2}	T _j = 125°C,	—	—	1.20	Volts
Slope Resistance, High-Level	r _{T2}	I = πI _{T(AV)} to I _{TSM}	—	—	0.818	mΩ
Switching Minimums						
Critical Rate-of-Rise of Off-State Voltage	dv/dt	T _j = 125°C, Gate Open, Linear to 0.67 V _{DRM}		1000		Volts/μs
Thermal Maximums						
Thermal Resistance, Junction-to-Case	R _{θ(J-C)}	Per Module, Both Conducting	—	—	0.085	°C/Watt
		Per SCR, Both Conducting	—	—	0.17	°C/Watt
Thermal Resistance, Case-to-Sink (Lubricated)	R _{θ(C-S)}	Per Module	—	—	0.05	°C/Watt
Gate Parameters Maximums						
Gate Current-to-Trigger	I _{GT}	T _j = 25°C, V _D = 12V	—	200	—	mA
Gate Voltage-to-Trigger	V _{GT}	T _j = 25°C, V _D = 12V	—	3.0	—	Volts
Non-Triggering Gate Voltage	V _{GDM}	T _j = 125°C, V _D = V _{DRM}	—	0.30	—	Volts
Peak Forward Gate Current	I _{GTM}	—	—	3.0	—	Amperes
Peak Reverse Gate Voltage	V _{GRM}	—	—	5.0	—	Volts

WARNING:

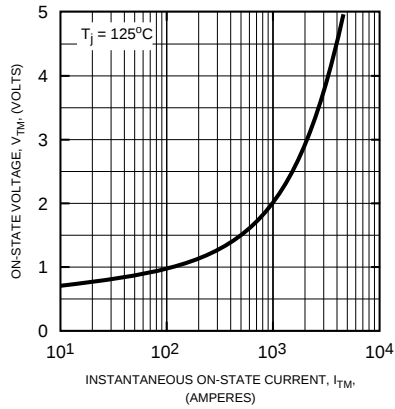
Internal insulation used is Beryllium Oxide.
 User should avoid grinding, crushing, or abrading these portions.
 Care must be exercised in properly disposing of unwanted devices.

CD63 _15

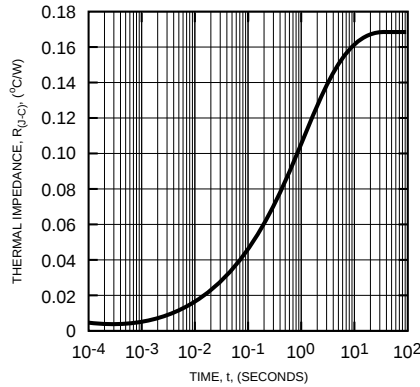
Dual SCR POW-R-BLOK™ Module

150 Amperes/1600 Volts

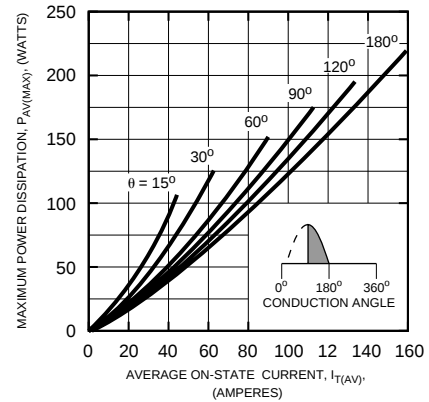
MAXIMUM ON-STATE FORWARD VOLTAGE DROP



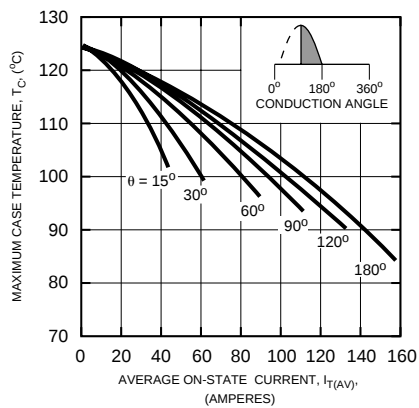
MAXIMUM TRANSIENT THERMAL IMPEDANCE (JUNCTION-TO-CASE)



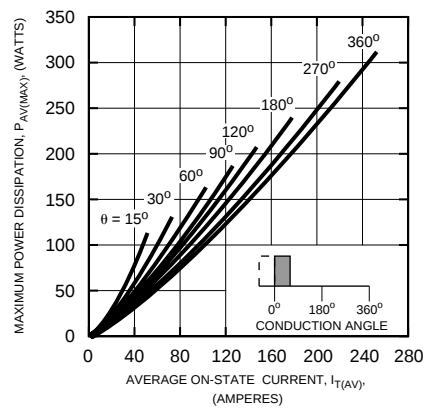
MAXIMUM ON-STATE POWER DISSIPATION (SINUSOIDAL WAVEFORM)



MAXIMUM ALLOWABLE CASE TEMPERATURE (SINUSOIDAL WAVEFORM)



MAXIMUM ON-STATE POWER DISSIPATION (RECTANGULAR WAVEFORM)



MAXIMUM ALLOWABLE CASE TEMPERATURE (RECTANGULAR WAVEFORM)

